CLAIMS

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3 1) A Vertical External Cavity Surface Emitting Laser 4 comprising: a semiconductor wafer structure, 5 containing a gain medium and a Bragg reflecting region; and a heatspreader associated with the wafer 6 7 structure such that the gain medium is located 8 between the heatspreader and the Bragg reflecting 9 region, wherein the heatspreader comprises a nonbirefringent material. 10

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12 2) A laser as claimed in Claim 1 wherein the 13 heatspreader comprises a first surface upon which is 14 located an anti-reflection coating.

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16 3) A Vertical External Cavity Surface Emitting Laser 17 comprising: a. semiconductor wafer structure 18 containing a gain medium and a Bragg reflecting 19 region; and a heatspreader associated with the wafer 20 structure such that the gain medium is located 21 between the heatspreader and the Bragg reflecting 22 region, wherein the heatspreader comprises a first 23 surface upon which is located an anti-reflection 24 coating.

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26 4) A laser as claimed in Claim 3 wherein the heatspreader comprises a non-birefringent material.

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29 5) A laser as claimed in any of Claims 2 to 4 wherein 30 the anti-reflection coating is optimised for 31 efficient operation with a refractive index of the 32 non-birefringent material and a lasing frequency of 33 the laser.

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2 6) A laser as claimed in any of Claims 2 to 5 wherein 3 the first surface of the heatspreader comprise a 4 wedge.

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6 7) A laser as claimed in any of the preceding claims
7 wherein the heatspreader comprises a single diamond
8 crystal.

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10 8) A laser as claimed in any of the preceding claims
11 wherein lasing is achieved by optical excitement of
12 the gain medium.

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14 9) A laser as claimed in any of claims 1 to 7 wherein
15 lasing is achieved by electrical excitement of the
16 gain medium.

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18 10) A laser as claimed in any of the preceding claims
19 wherein the laser further comprises an intracavity
20 polarisation selecting element that provides a first
21 means for selecting the operating frequency of the
22 laser.

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24 11) A laser as claimed in Claim 10 wherein the 25 intracavity polarisation selecting element comprises 26 a birefringent filter orientated at Brewster's angle.

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28 12) A laser as claimed in any of the preceding claims
29 wherein the laser further comprises an intracavity
30 etalon that provides a second means for selecting the
31 operating frequency of the laser.

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1 13) A laser as claimed in any of the preceding claims
2 wherein the laser further comprises an external
3 reference cavity that allows for the frequency
4 stabilisation of the laser output to a side of a
5 transmission peak of the external cavity.

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14) A laser as claimed in any of the preceding claims wherein the laser comprises a three mirror folded cavity arrangement.

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11 15) A laser as claimed in Claim 14 wherein the laser
12 further comprises a cavity mirror mounted on a first
13 piezoelectric crystal and an output coupler mounted
14 on a second piezoelectric crystal wherein the
15 combined movement of the cavity mirror and the output
16 coupler provides a first means for frequency tuning
17 the output of the laser.

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19 16) A laser as claimed in Claim 14 or 15 wherein the
20 laser further comprises a pair of Brewster plates and
21 a cavity mirror mounted on a piezoelectric crystal
22 wherein the combined movement of the Brewster plates
23 and the cavity mirror provide a second means for
24 frequency tuning the output of the laser.

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17) A frequency scanning Vertical External Cavity Surface 26 Emitting Laser suitable for use in high resolution 27 spectroscopy experiments comprising: apparatus for 28 selecting and stabilising the operating frequency of 29 apparatus for scanning the operating 30 laser; semiconductor frequency of the laser; a 31 structure containing a gain medium and a 32 reflecting region; and a heatspreader associated with 33

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1	•	the wafer structure such that the gain medium is
2		located between the heatspreader and the Bragg
3		reflecting region, wherein the heatspreader comprises
4		a non-birefringent material.
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6	18)	A laser as claimed in Claim 17 wherein the
7	-	heatspreader comprises a first surface upon which is
8		located an anti-reflection coating.
9		
10	19)	A laser as claimed in Claim 17 or 18 wherein the
11		apparatus for selecting and stabilising the operating
12	٠,	frequency of the laser comprises an intracavity
13		polarisation selecting element that provides a first
14		means for selecting the operating frequency of the
15		laser
16		
17	20)	A laser as claimed in Claim 19 wherein the apparatus
18		for selecting and stabilising the operating frequency
19		of the laser further comprises an intracavity etalon
20		that provides a second means for selecting the
21		operating frequency of the laser.
22		
23	21)	A laser as claimed in Claim 20 wherein the apparatus
24		for selecting and stabilising the operating frequency
25		of the laser further comprises an external reference
26		cavity that allows for the frequency stabilisation of
27		the laser output to a side of a transmission peak of
28		the external cavity.
29		
30	22)	A laser as claimed in any of claims 17 to 21 wherein
31		the apparatus for scanning the operating frequency of
32		the laser comprises a cavity mirror mounted on a
33		first piezoelectric crystal and an output coupler

1		mounted on a second piezoelectric crystal wherein the
2		combined movement of the cavity mirror and the output
3		coupler provides a first means for tuning the
4		frequency output of the laser.
5		
6	23)	A laser as claimed in any of claims 17 to 22 wherein
7	,	the apparatus for scanning the operating frequency of
8		the laser comprises a pair of Brewster plates and a
9		cavity mirror mounted on a piezoelectric crystal
LO		wherein the combined movement of the Brewster plates
L1		and the cavity mirror provides a second means for
L2		tuning the frequency output of the laser.
L3		
L 4	24)	A laser as claimed in any of claims 18 to 23 wherein
L5		the anti-reflection coating is optimised for
L6		efficient operation with a refractive index of the
L7		non-birefringent material and a lasing frequency of
L8		the laser.
L9		
20	25)	A laser as claimed in any of claims 17 to 24 wherein
21		the first surface of the heatspreader comprise a
22	•	wedge.
23		
24	26)	A laser as claimed in any of claims 17 to 25 wherein

the heatspreader comprises a single diamond crystal.

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